

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Constantin Bulucea and Rebecca Rossen
 Assignee: Siliconix incorporated
 Title: TRENCH DMOS POWER TRANSISTOR WITH FIELD-SHAPING
 BODY PROFILE AND THREE-DIMENSIONAL GEOMETRY
 Serial No.: unknown Filed: herewith
 Examiner: J. Carroll Group Art Unit: 2508
 Attorney Docket No.: M-799-3C US

San Jose, California
 May 30, 1995

COMMISSIONER OF PATENTS AND TRADEMARKS
 Washington, D. C. 20231

PRELIMINARY AMENDMENT

Sir:

The present application is a file-wrapper continuation of the copending application ("Parent Application"), serial no. 08/086,976, filed on July 2, 1993, now abandoned. In response to the final office action in the Parent Application, mailed on December 29, 1994, Applicants amend the present application as follows:

In the Claims

Please add Claims 30-53 as follows:

30. A trench DMOS transistor cell, comprising:

a substrate of semiconductor material of heavily doped first electrical conductivity type having a top surface;

a first covering layer of semiconductor material of first electrical conductivity type having a top surface and being contiguous to and overlying the substrate top surface;

a second covering layer of semiconductor material of second electrical conductivity type having a top surface and being contiguous to the top surface of the first covering layer and extending vertically downward from the top surface of the first covering layer into an upper

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